Joon-Hyung Lee

List of Publications by Year
in descending order

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Version: 2024-02-01

161 papers	2,528 citations	185998 28 h-index	264894 42 g-index
161 all docs	161 docs citations	161 times ranked	2816 citing authors

#	Article	IF	Citations
1	Synthesis of Cs2TeI6 thin film and its NO2 gas-sensing properties under blue-light illumination. Scripta Materialia, 2022, 207, 114305.	2.6	11
2	Growth and NO2 sensing properties of Cs2SnI6 thin film. Materials Research Bulletin, 2022, 147, 111628.	2.7	4
3	Oxygen Migration Energy in La and Y Co-doped CeO2: Effect of Lattice Constant and Grain Boundary Segregation. Journal of Science: Advanced Materials and Devices, 2022, , 100450.	1.5	0
4	Evaluation of alumina slurry dispersion by nuclear magnetic resonance relaxation as a comparison to conventional dispersion evaluation methods. Magnetic Resonance in Chemistry, 2022, 60, 877-883.	1.1	4
5	Effect of tin (II and IV) iodide doping on organicâ€“inorganic bismuth (III) iodide perovskite. Materials Letters, 2020, 262, 127166.	1.3	4
6	Growth and gas sensing properties of methylammonium tin iodide thin film. Scripta Materialia, 2020, 178, 108-113.	2.6	14
7	Room-temperature NO2 sensor based on a hybrid nanomaterial of methylammonium tin iodide submicron spheres and tin dioxide nanowires. Scripta Materialia, 2020, 188, 107-111.	2.6	15
8	Effects of oxygen partial pressure on the structural and electrical properties of Al and Sb co-doped p-type ZnO thin films grown by pulsed laser deposition. Thin Solid Films, 2020, 708, 138130.	0.8	7
9	Growth and NO₂-Sensing Properties of Biaxial p-SnO/n-ZnO Heterostructured Nanowires. ACS Applied Materials & Interfaces, 2020, 12, 34274-34282.	4.0	22
10	Oxygen nonstoichiometry and electrical properties of La2â€“xSrxNiO4+Î´ (0â€‰â‰â€‰xâ€‰â‰â€‰0.5). Journal of the Korean Ceramic Society, 2020, 57, 416-422.	1.1	10
11	Effects of pH and reaction temperature on hydroxyapatite powders synthesized by precipitation. Springer Series in Emerging Cultural Perspectives in Work, Organizational, and Personnel Studies, 2020, 57, 56-64.	1.5	19
12	Reaction sintering behavior and electrical properties of a Ga-doped ITO system. Ceramics International, 2019, 45, 20678-20683.	2.3	0
13	High-Voltage, Room-Temperature Liquid Metal Flow Battery Enabled by Na-K|K-Î²â€³-Alumina Stability. Joule, 2018, 2, 1287-1296.	11.7	48
14	Effect of Ni doping on the structural, electrical, and optical properties of transparent CuCrO2 films grown using pulsed laser deposition. Ceramics International, 2018, 44, 17743-17748.	2.3	20
15	Fabrication of Nanostructured SnO by Chemical Vapor Transport Process. Applied Science and Convergence Technology, 2018, 27, 140-143.	0.3	0
16	Effect of Oxygen Partial Pressure and Sintering Temperature on the Evaporation of Elements during Sintering in In-Sn-Zn-O Transparent Conducting Oxide Systems. Applied Science and Convergence Technology, 2018, 27, 178-183.	0.3	2
17	Effect of a ZnO buffer layer on structural and electrical properties of ZnO:Al,P thin films grown by RF magnetron sputtering. Ceramics International, 2017, 43, 11163-11169.	2.3	12
18	Fabrication of SnO2 Nanowire Networks on a Spherical Sn Surface by Thermal Oxidation. Journal of Electronic Materials, 2017, 46, 6070-6077.	1.0	4

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19	Ionic conductivity and relaxations of In-doped GDC (gadolinium doped ceria) ceramics. Ceramics International, 2017, 43, 11792-11798.	2.3	16
20	Structural and Optical Characteristics of Zn-Rich In₂O₃â€“SnO₂â€“ZnO (ITZO) Thin Films Prepared by Radio Frequency Magnetron Sputtering. Journal of Nanoelectronics and Optoelectronics, 2017, 12, 598-601.	0.1	3
21	Effect of Li2O content and sintering temperature on the grain growth and electrical properties of Gd-doped CeO2 ceramics. Ceramics International, 2016, 42, 11170-11176.	2.3	17
22	Effect of Li doping on sintering characteristics and microstructural behavior of yttria-stabilized zirconia. Ceramics International, 2016, 42, 17339-17346.	2.3	5
23	Broadband pH-Sensing Organic Transistors with Polymeric Sensing Layers Featuring Liquid Crystal Microdomains Encapsulated by Di-Block Copolymer Chains. ACS Applied Materials & Interfaces, 2016, 8, 23862-23867.	4.0	24
24	Physical force-sensitive touch responses in liquid crystal-gated-organic field-effect transistors with polymer dipole control layers. Organic Electronics, 2016, 28, 184-188.	1.4	6
25	Effect of oxygen pressure on the p-type conductivity of Ga, P co-doped ZnO thin film grown by pulsed laser deposition. Ceramics International, 2016, 42, 4136-4142.	2.3	22
26	Study of Dry Etching of SnO thin films using a Inductively Coupled Plasma. Journal of the Korean Institute of Surface Engineering, 2016, 49, 98-103.	0.1	0
27	Ultrasensitive tactile sensors based on planar liquid crystal-gated-organic field-effect transistors with polymeric dipole control layers. RSC Advances, 2015, 5, 56904-56907.	1.7	6
28	Synthesis of submicron-sized rods and trees of Cu 2 O by radio-frequency magnetron sputtering. Vacuum, 2015, 111, 60-67.	1.6	3
29	Structural and Electrical Properties of (Al or Ga) and P Co-Doped ZnO Thin Films Prepared by Pulsed Laser Deposition. Journal of Nanoelectronics and Optoelectronics, 2015, 10, 449-454.	0.1	3
30	Effect of Oxygen Plasma Treatment on <I>p</I>-Type Electrical Properties of Amorphous La₂NiO_{4+<I>Î´</I>} Thin Films. Journal of Nanoelectronics and Optoelectronics, 2015, 10, 475-479.	0.1	2
31	Transfer Characteristics of a-IGZO Thin Film Transistors Prepared with Different RF Powers. Journal of Nanoelectronics and Optoelectronics, 2015, 10, 520-523.	0.1	1
32	Optoelectronic Characteristics of Devices with Conducting Polymer Layers: A Planar Sensor Approach. Journal of Nanoelectronics and Optoelectronics, 2015, 10, 440-443.	0.1	2
33	Sintering Behavior and Electrochemical Properties of (Gd₀_{.1}Ce₀_{.9}O₁_{.95})_{<I>x</I>}(Y<SU 10, 582-587.	0.1	0
34	Specific Intracellular Uptake of Herceptin-Conjugated CdSe/ZnS Quantum Dots into Breast Cancer Cells. BioMed Research International, 2014, 2014, 1-9.	0.9	15
35	Transmission Electron Microscopy Study of 3.2 YSZ Single Crystals Manufactured by the Skull Melting Method. Journal of Nanoscience and Nanotechnology, 2014, 14, 7961-7964.	0.9	6
36	Touch sensors based on planar liquid crystal-gated-organic field-effect transistors. AIP Advances, 2014, 4, 097109.	0.6	6

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37	Effect of sintering temperature and P2O5 concentration on the grain shape and grain growth behavior in the ZnOâ€“P2O5 system. Ceramics International, 2014, 40, 10143-10147.	2.3	1
38	Structure and NH3 sensing properties of SnO thin film deposited by RF magnetron sputtering. Sensors and Actuators B: Chemical, 2014, 194, 134-141.	4.0	49
39	Biosensor utilizing a liquid crystal/water interface functionalized with poly(4-cyanobiphenyl-4â€²-oxyundecylacrylate-b-((2-dimethyl amino) ethyl methacrylate)). Colloids and Surfaces B: Biointerfaces, 2014, 121, 400-408.	2.5	33
40	Liquid crystal-based biosensors using a strong polyelectrolyte-containing block copolymer, poly(4-cyanobiphenyl-4â€²-oxyundecylacrylate)-b-poly(sodium styrene sulfonate). Macromolecular Research, 2014, 22, 888-894.	1.0	16
41	Strong addition effect of charge-bridging polymer in polymer:fullerene solar cells with low fullerene content. RSC Advances, 2014, 4, 24914-24921.	1.7	4
42	Folate Ligand Anchored Liquid Crystal Microdroplets Emulsion for in Vitro Detection of KB Cancer Cells. Langmuir, 2014, 30, 10668-10677.	1.6	57
43	Real-time liquid crystal-based biosensor for urea detection. Analytical Methods, 2014, 6, 5753-5759.	1.3	26
44	Effect of <scp><scp>Ba</scp></scp> Nonstoichiometry in <scp><scp>Ba</scp></scp>_x(<scp><scp>Zr</scp></scp>_{0.8}<scp><scp>Y</scp></scp><sub>0.2</sub on Population of 5â€Coordinated Y. Journal of the American Ceramic Society, 2014, 97, 3749-3754.	1.9	5
45	H2S-sensing properties of Cu2O submicron-sized rods and trees synthesized by radio-frequency magnetron sputtering. Sensors and Actuators B: Chemical, 2014, 202, 330-338.	4.0	32
46	Effects of Temperature, Target/Substrate Distance, and Background Pressure on Growth of ZnO Nanorods by Pulsed Laser Deposition. Journal of Nanoscience and Nanotechnology, 2014, 14, 9020-9024.	0.9	7
47	Electrical and Optical Properties of Amorphous ITZO Deposited at Room Temperature by RF Magnetron Sputtering. Journal of the Korean Institute of Surface Engineering, 2014, 47, 239-243.	0.1	3
48	Fabrication Process of Single CuO Nanowire Devices. Applied Science and Convergence Technology, 2014, 23, 134-138.	0.3	1
49	Thermal expansion behavior of La-doped (Ba0.5Sr0.5Co0.8Fe0.2)O3âˆ’Î´ cathode material. Ceramics International, 2013, 39, 8267-8271.	2.3	12
50	The aging effect on the low temperature mechanical strength of 3.2YSZ single crystals manufactured by the Skull melting method. Ceramics International, 2013, 39, 2031-2036.	2.3	5
51	Effect of sintering atmospheres on the densification behavior of CuO ceramics. Ceramics International, 2013, 39, S315-S319.	2.3	2
52	Growth of CuO nanowires on graphene-deposited Cu foil by thermal oxidation method. Journal of Crystal Growth, 2013, 384, 100-106.	0.7	4
53	Adhesion behavior between yttrium-stabilized zirconia added La0.8Ca0.2Cr0.9Co0.1O3âˆ’Î´ interconnector and yttrium-stabilized zirconia-based substrate. Ceramics International, 2013, 39, 8737-8741.	2.3	1
54	Structural and Electrical Properties of Al and P Co-Doped ZnO Thin Films Prepared by Pulsed Laser Deposition. Journal of Nanoelectronics and Optoelectronics, 2013, 8, 489-492.	0.1	4

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55	Formation of SnO₂ Layers on SnO Thin Films and Their CH₄ Sensing Properties. Journal of Nanoelectronics and Optoelectronics, 2013, 8, 479-483.	0.1	2
56	Microstructural and Electrical Characteristics of Preferential Growth Direction Controlled CuCrO₂ Thin Films. Journal of Nanoelectronics and Optoelectronics, 2013, 8, 579-583.	0.1	2
57	The Effect of Annealing Treatment on the Electrical Properties of Li-Ga Co-Doped ZnO. Journal of Nanoelectronics and Optoelectronics, 2013, 8, 530-534.	0.1	0
58	Low Temperature Growth and Optical Properties of ZnO Nanowires Using an Aqueous Solution Method. Journal of Nanoscience and Nanotechnology, 2012, 12, 1415-1420.	0.9	0
59	Characteristics of Sn and Zn co-substituted In2O3 thin films prepared by RF magnetron sputtering. Current Applied Physics, 2012, 12, S89-S93.	1.1	5
60	Optical band gap modulation by Mg-doping in In2O3(ZnO)3 ceramics. Ceramics International, 2012, 38, 6693-6697.	2.3	13
61	Preferential growth orientations of CuCrO2 films grown by pulsed laser deposition. Current Applied Physics, 2012, 12, S123-S126.	1.1	8
62	Effect of SiC Addition on Sintering Behavior and Properties of Indium Tin Oxide. Journal of Nanoelectronics and Optoelectronics, 2012, 7, 559-563.	0.1	1
63	Structural, Optical, and Electrical Properties of p-Type SnO Thin Films Deposited by Reactive RF Magnetron Sputtering. Journal of Nanoelectronics and Optoelectronics, 2012, 7, 475-478.	0.1	2
64	Expanded Solubility and Densification Behavior of Li-Ga Co-Doped ZnO. Journal of Nanoelectronics and Optoelectronics, 2012, 7, 575-579.	0.1	1
65	Effects of Zn Content on Transfer Characteristics of Indium-Gallium-Zinc Oxide Thin-Film Transistors. Journal of Nanoelectronics and Optoelectronics, 2012, 7, 471-474.	0.1	0
66	Effect of the Sintering Temperature and Atmosphere on the Microstructural Evolution and Shrinkage Behavior of CuO Ceramics. Journal of the Korean Ceramic Society, 2012, 49, 528-534.	1.1	0
67	Low temperature processing of indium-tin-zinc oxide channel layers in fabricating thin-film transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, .	0.6	5
68	Co-doping effect of Zn and Sb in SnO2: Valence stabilization of Sb and expanded solubility limit. Ceramics International, 2011, 37, 2723-2726.	2.3	8
69	Structural properties of the epitaxial CuCr0.95Mg0.05O2 thin films on c-plane sapphire substrates by pulsed laser deposition. Journal of Crystal Growth, 2011, 326, 9-13.	0.7	12
70	Effects of channel dimensions on performance of a-InGaZnO4 thin-film transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, .	0.6	27
71	Structural and Electrical Properties of Al and B Co-Doped ZnO Thin Films. Journal of Nanoelectronics and Optoelectronics, 2011, 6, 301-305.	0.1	5
72	Effects of Post-Annealing Treatments on the Transfer Characteristics of Amorphous Indium-Gallium-Zinc Oxide Thin Film Transistors. Journal of Nanoelectronics and Optoelectronics, 2011, 6, 310-314.	0.1	6

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73	UV Photoresponse of Ag-Doped Multiple ZnO Nanowires. Journal of Nanoelectronics and Optoelectronics, 2011, 6, 244-248.	0.1	0
74	Sintering Behavior and Electrical Properties of In2O3 Ceramics with ZnO and Sb2O5 Co-Substitution. Journal of Nanoelectronics and Optoelectronics, 2011, 6, 348-352.	0.1	0
75	Phase development and crystallization of CuAlO2 thin films prepared by pulsed laser deposition. Journal of the European Ceramic Society, 2010, 30, 509-512.	2.8	33
76	Effects of ambient atmosphere on the transfer characteristics and gate-bias stress stability of amorphous indium-gallium-zinc oxide thin-film transistors. Applied Physics Letters, 2010, 96, .	1.5	121
77	Fabrication of p-channel thin-film transistors using CuO active layers deposited at low temperature. Applied Physics Letters, 2010, 97, .	1.5	97
78	SnO2: CuSb2O6 Thin Films Prepared by Pulsed Laser Deposition. Integrated Ferroelectrics, 2010, 115, 34-40.	0.3	2
79	Catalyst-Free Patterned Growth of Well-Aligned ZnO Nanowires on ITO Substrates Using an Aqueous Solution Method and Lithography Process. Journal of Nanoelectronics and Optoelectronics, 2010, 5, 186-190.	0.1	3
80	SnO₂ and ZnO Co-Doping Effect in In₂O₃(ZnO)₃ Transparent Conducting Ceramics. Journal of Nanoelectronics and Optoelectronics, 2010, 5, 262-266.	0.1	1
81	Phase Development and Electrical Characteristics of <I>n</I>-Type Semiconductive Transparent In₂O₃(ZnO)₂ Ceramics with ZnO/SnO₂ Co-Substitution. Journal of Nanoelectronics and Optoelectronics, 2010, 5, 232-237.	0.1	0
82	Transfer characteristics and bias-stress stability of amorphous indium zinc oxide thin-film transistors. Journal of Vacuum Science & Technology B, 2009, 27, 622-625.	1.3	18
83	Effects of oxygen partial pressure on the preferential orientation and surface morphology of ITO films grown by RF magnetron sputtering. Journal of Electroceramics, 2009, 23, 169-174.	0.8	52
84	Growth of CuInO2 thin film using highly dense Cu2Oâ€“In2O3 composite targets. Thin Solid Films, 2009, 518, 1234-1237.	0.8	16
85	Electrical and electromechanical properties of leadâ€“potassiumâ€“yttriumâ€“niobate ceramicsâ€”piezoelectric applications. Journal of Physics and Chemistry of Solids, 2009, 70, 1231-1241.	1.9	8
86	Doping of Nitrogen in Li-Al doped ZnO by RF Magnetron Sputtering. Journal of the Korean Physical Society, 2009, 54, 1293-1296.	0.3	4
87	Growth of Mg Doped CuCrO₂by Pulsed Laser Deposition. Journal of the Korean Institute of Surface Engineering, 2009, 42, 68-72.	0.1	3
88	Deep etch-induced damage during ion-assisted chemical etching of sputtered indiumâ€“zincâ€“oxide films in Ar/CH4/H2 plasmas. Thin Solid Films, 2008, 516, 2869-2873.	0.8	2
89	Synthesis, electrical and electromechanical properties of a tungsten-bronze ceramic oxide: Pb0.68K0.64Nb2O6. Physica B: Condensed Matter, 2008, 403, 2079-2087.	1.3	23
90	LEAD BARIUM POTASSIUM SODIUM NIOBATE CERAMICS FOR PIEZOELECTRIC APPLICATIONS. International Journal of Modern Physics B, 2008, 22, 1961-1976.	1.0	3

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91	Electrical, electromechanical and structural studies of lead potassium samarium niobate ceramics. Journal of Alloys and Compounds, 2008, 464, 497-507.	2.8	70
92	FERROELECTRIC AND PIEZOELECTRIC PROPERTIES OF Gd3+ AND Y3+ MODIFIED PKN ELECTROCERAMICS. Modern Physics Letters B, 2008, 22, 1515-1523.	1.0	0
93	INFLUENCE OF SAMARIUM SUBSTITUTION ON IMPEDANCE DIELECTRIC AND ELECTROMECHANICAL PROPERTIES OF Pb(1-x)K2xNb2O6. International Journal of Modern Physics B, 2007, 21, 931-945.	1.0	13
94	Influence of the film properties on the plasma etching dynamics of rf-sputtered indium zinc oxide layers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2007, 25, 659-665.	0.9	9
95	Grain Growth Kinetics of Cobalt-Doped SnO₂ by Varying Nb₂O₅ Content. Materials Science Forum, 2007, 534-536, 529-532.	0.3	4
96	High Density Inductively Coupled Plasma Etching of Zinc-Oxide(ZnO) and Indium-Zinc Oxide(IZO). ECS Transactions, 2007, 6, 239-247.	0.3	0
97	MICROSTRUCTURE EVOLUTION AND DIELECTRIC PROPERTIES OF K3Li2Nb5O15 and BaTiO3 COMPOSITES. Integrated Ferroelectrics, 2007, 87, 77-84.	0.3	0
98	EFFECTS OF Ni PARTICLE SIZE ON DIELECTRIC PROPERTIES OF PMMA-Ni-BaTiO3 COMPOSITES. Integrated Ferroelectrics, 2007, 87, 85-93.	0.3	10
99	Transparent amorphous indium zinc oxide thin-film transistors fabricated at room temperature. Applied Physics Letters, 2007, 90, 022106.	1.5	115
100	Comparison of plasma chemistries for the dry etching of bulk single-crystal zinc-oxide and rf-sputtered indiumâ€“zinc-oxide films. Applied Surface Science, 2007, 253, 9228-9233.	3.1	7
101	Effect of Bi2O3 content on sintering and crystallization behavior of low-temperature firing Bi2O3â€“B2O3â€“SiO2 glasses. Journal of the European Ceramic Society, 2007, 27, 819-824.	2.8	57
102	Characterization of the low temperature firing BaOâ€“B2O3â€“SiO2 glass: The effect of BaO content. Journal of the European Ceramic Society, 2007, 27, 825-829.	2.8	38
103	Reaction-sintering behavior of nanocrystalline indium tin oxide with varying SnO2 content and particle size. Scripta Materialia, 2007, 56, 293-296.	2.6	16
104	Effect of structure change on thermal and dielectric characteristics in low-temperature firing Bi2O3â€“B2O3â€“ZnO glasses. Journal of Materials Science, 2007, 42, 4260-4264.	1.7	13
105	Dry etching of zinc-oxide and indium-zinc-oxide in IBr and BI3 plasma chemistries. Applied Surface Science, 2007, 253, 3773-3778.	3.1	16
106	Effect of forming pressure on densification behavior of nanocrystalline ITO powder. Journal of the European Ceramic Society, 2007, 27, 807-812.	2.8	15
107	Effect of BaO content on the sintering and physical properties of BaOâ€“B2O3â€“SiO2 glasses. Journal of Non-Crystalline Solids, 2006, 352, 821-826.	1.5	44
108	Synthesis and Electrical Characterization of the Polymorphic Indium Tin Oxide Nanocrystalline Powders. Journal of the American Ceramic Society, 2006, 89, 3431-3436.	1.9	21

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109	High-density plasma etching of indiumâ€“zinc oxide films in Ar/Cl2 and Ar/CH4/H2 chemistries. Applied Surface Science, 2006, 253, 2752-2757.	3.1	13
110	Effect of synthesis conditions on the properties of LiFePO4 for secondary lithium batteries. Journal of Power Sources, 2006, 159, 237-240.	4.0	60
111	Preparation and sintering of nanocrystalline ITO powders with different SnO2 content. Journal of the European Ceramic Society, 2006, 26, 73-80.	2.8	63
112	Low-temperature sintering and microwave dielectric characteristics of Ba2Ti9O20 ceramics. Journal of the European Ceramic Society, 2006, 26, 2111-2115.	2.8	12
113	Sintering behavior and microwave dielectric characteristics of BaOâ€“Sm2O3â€“4TiO2 ceramics with B2O3 and BaB2O4 addition. Journal of the European Ceramic Society, 2006, 26, 2129-2133.	2.8	15
114	Effect of borate glass additives on the sintering behaviour and dielectric properties of BaTi4O9 ceramics. Journal of the European Ceramic Society, 2006, 26, 2135-2138.	2.8	19
115	Co-doping effect of SnO2 and ZnO in In2O3 ceramics: Change in solubility limit and electrical properties. Solid State Ionics, 2006, 177, 601-605.	1.3	12
116	Sintering behaviors and electrical properties of transparent conducting In6Sn2â€“x ZnxO13â€“x ceramics with different Sn/Zn ratio. Journal of Electroceramics, 2006, 17, 1057-1061.	0.8	3
117	Dielectric, thermal and sintering behavior of BaO-B2O3-SiO2 glasses with the addition of Al2O3. Journal of Electroceramics, 2006, 17, 359-363.	0.8	12
118	Microstructure evolution and dielectric properties of Ba5-xNa2xNb10O30 ceramics with different Baâ€“Na Ratios. Journal of Solid State Electrochemistry, 2006, 10, 18-23.	1.2	28
119	Crystal structures, electrical conductivities and electrochemical properties of LiCo1â^'xMgxO2 (0â‰xâ‰0.11). Journal of Power Sources, 2006, 159, 233-236.	4.0	41
120	Microstructure evolution and dielectric properties of K3Li2Nb5O15 and PbTiO3 composites. Materials Letters, 2006, 60, 3426-3430.	1.3	2
121	Effects of Zn content on structural and transparent conducting properties of indium-zinc oxide films grown by rf magnetron sputtering. Journal of Vacuum Science & Technology B, 2006, 24, 2737.	1.3	25
122	Effects of BaTiO3 on dielectric behavior of BaTiO3â€“Niâ€“polymethyl methacrylate composites. Applied Physics Letters, 2006, 89, 132910.	1.5	70
123	EFFECT OF YTTRIUM ON DIELECTRIC, PYROELECTRIC AND PIEZOELECTRIC PROPERTIES OF PBN FERROELECTRICS. International Journal of Modern Physics B, 2006, 20, 3081-3091.	1.0	3
124	Crystallization of indium tin oxide thin films prepared by RF-magnetron sputtering without external heating. Thin Solid Films, 2005, 474, 127-132.	0.8	47
125	Densification of nanocrystalline ITO powders in fast firing: effect of specimen mass and sintering atmosphere. Materials Research Bulletin, 2005, 40, 395-404.	2.7	29
126	Electrical Properties of K3Li2Nb5O15 Ceramics with Substitutions of Ba and Sr. Integrated Ferroelectrics, 2005, 69, 21-31.	0.3	3

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127	Densification Behavior and Electrical Properties of K3Li2(Nb1 - xTax)5O15 Ceramics. Integrated Ferroelectrics, 2005, 69, 11-20.	0.3	2
128	Effect of Ta2O5 Content on Microstructure and Dielectric Properties of Ba2NbNb5(1 - x)Ta5xO15 Ceramic. Integrated Ferroelectrics, 2005, 69, 33-42.	0.3	4
129	MICROSTRUCTURE EVOLUTION AND DIELECTRIC PROPERTIES OF (Ba1â^'xSrx)4Na2Nb10O30 CERAMICS WITH DIFFERENT Ba/Sr RATIOS. Integrated Ferroelectrics, 2005, 74, 61-70.	0.3	4
130	Chemically Induced Interface Migration in PZT System During Controlling of PbO Content. Integrated Ferroelectrics, 2004, 63, 117-120.	0.3	1
131	Sintering behavior of Y-doped ZrO2 ceramics: the effect of Al2O3 and Nb2O5 addition. Solid State Ionics, 2004, 172, 413-416.	1.3	24
132	Phase development procedure of In2O3(ZnO)3 ceramics and its sintering behavior. Solid State Ionics, 2004, 172, 425-429.	1.3	17
133	Effect of ZnO addition in In2O3 ceramics: defect chemistry and sintering behavior. Solid State Ionics, 2004, 172, 431-434.	1.3	26
134	Phase Stability of Tungsten-Bronze-Structured KLN Ceramics: Effect of Excess Nb2O5. Journal of Electroceramics, 2004, 13, 847-850.	0.8	4
135	Phase Transformation Behavior of Nanocrystalline ITO Powders during Heat-Treatment: Oxygen Partial Pressure Effect. Journal of Electroceramics, 2004, 13, 851-855.	0.8	10
136	Effect of sintering atmosphere on densification and dielectric characteristics in Sr0.5Ba0.5Nb2O6 ceramics. Journal of the European Ceramic Society, 2004, 24, 1031-1035.	2.8	14
137	Phase development and microwave dielectric properties of BaOâ€"xSm2O3â€"4.5TiO2 (x = 0â€"1.25) ceramics. Materials Chemistry and Physics, 2003, 79, 282-285.	2.0	7
138	Effect of Nb2O5 content on dielectric characteristics of tungstenâ€"bronze-structured KLN ceramics. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 99, 483-486.	1.7	10
139	Dielectric and pyroelectric properties of BSNN ceramics: effect of Ba/Sr ratio and La2O3 addition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 98, 279-285.	1.7	41
140	Effect of Nb2O5 Content on Microstructure and Dielectric Properties of Ba2-2xNa1-xNb5O15-5x/2 Ceramics. International Journal of Modern Physics B, 2003, 17, 1273-1278.	1.0	5
141	Microstructure and Dielectric Properties of Tungsten Bronze Structured KLN and BNN Ceramics: TiO2 Effect. International Journal of Modern Physics B, 2003, 17, 1267-1272.	1.0	3
142	Influence of Pr 2 O 3 and Nd 2 O 3 on Ferroelectric and Pyroelectric Properties of Tungsten Bronze Structured BSNN Ceramics. Ferroelectrics, Letters Section, 2003, 30, 25-39.	0.4	10
143	Dielectric Characteristics of Ferroelectric Sr 0.7 Ba 0.3 Nb 2 O 6 Ceramics with Different Nb 2 O 5 Content. Ferroelectrics, 2002, 270, 123-128.	0.3	0
144	Site Occupancy and Dielectric Characteristics of Strontium Barium Niobate Ceramics: Sr/Ba Ratio Dependence. Japanese Journal of Applied Physics, 2002, 41, 7042-7047.	0.8	36

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145	Origin of Abnormal Grain Growth in Tungsten Bronze Structured Ferroelectric SrxBa1-xNb2O6Ceramics. Japanese Journal of Applied Physics, 2002, 41, 7048-7052.	0.8	8
146	Influence of Nb 2 O 5 Content on Dielectric Characteristics of Ferroelectric SBN Ceramics. Integrated Ferroelectrics, 2002, 47, 245-257.	0.3	1
147	Rapid rate sintering of nanocrystalline indium tin oxide ceramics: particle size effect. Materials Letters, 2002, 52, 114-119.	1.3	68
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